

## Dual N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ☒ Surface-mounted package
- ☒ Low Thermal Resistance

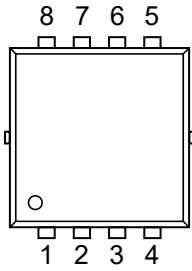
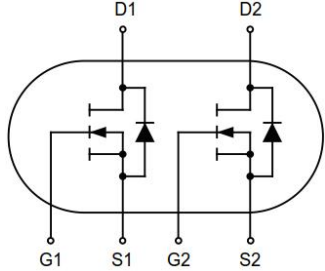
#### 1.2 Applications

- ☒ Motor drivers
- ☒ DC - DC Converter

#### 1.3 Quick reference

- ☒  $BV \geq 30\text{ V}$
- ☒  $P_D \leq 20.8\text{ W}$
- ☒  $I_D \leq 42\text{ A}$
- ☒  $R_{DS(ON)} \leq 6.5\text{ m}\Omega @V_{GS} = 10\text{ V}$
- ☒  $R_{DS(ON)} \leq 11\text{ m}\Omega @V_{GS} = 4.5\text{ V}$

### 2. Pin Description

| Pin | Description | Simplified Outline                                                                                                     | Symbol                                                                                |
|-----|-------------|------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Source(S1)  |  <p>Top View<br/>PDFN3.3x3.3-8L</p> |  |
| 2   | Gate(G1)    |                                                                                                                        |                                                                                       |
| 3   | Source(S2)  |                                                                                                                        |                                                                                       |
| 4   | Gate(G2)    |                                                                                                                        |                                                                                       |
| 5,6 | Drain(D2)   |                                                                                                                        |                                                                                       |
| 7,8 | Drain(D1)   |                                                                                                                        |                                                                                       |

## 3. Limiting Values

| Symbol          | Parameter                                        | Conditions                                    | Min | Max      | Unit                 |
|-----------------|--------------------------------------------------|-----------------------------------------------|-----|----------|----------------------|
| $V_{DS}$        | Drain-Source Voltage                             | $T_C=25^{\circ}\text{C}$                      | 30  | -        | V                    |
| $V_{GS}$        | Gate-Source Voltage                              | $T_C=25^{\circ}\text{C}$                      | -   | $\pm 20$ | V                    |
| $I_D$           | Drain Current (DC)                               | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 42       | A                    |
|                 |                                                  | $T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$ | -   | 27       | A                    |
| $I_{DM}^*$      | Pulsed Source Current                            | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 168      | A                    |
| $P_D$           | Power Dissipation                                | $T_C=25^{\circ}\text{C}$                      | -   | 20.8     | W                    |
| $E_{AS}$        | Single Pulsed Avalanche Energy                   | $V_{DD}=15\text{ V}, L=0.3\text{ mH}$         | -   | 60       | mJ                   |
| $T_J, T_{stg}$  | Operating Junction and Storage Temperature Range |                                               | -55 | 150      | $^{\circ}\text{C}$   |
| $R_{\theta JA}$ | Thermal Resistance-Junction to Ambient           |                                               | -   | 50       | $^{\circ}\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case              |                                               | -   | 6        |                      |

Notes:

- \* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- \*\* Surface mounted on  $1\text{ in}^2$  pad area,  $t \leq 10\text{ sec}$ .
- \*\*\* Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking                                                                                                                           |
|--------------|-----------------------------------------------------------------------------------------------------------------------------------|
| KJ0603QD     | <div style="background-color: black; color: white; padding: 5px; display: inline-block;"> <b>0603QD</b><br/> <b>XXXXXX</b> </div> |

## 5. Ordering Code

| Product Name | Package         | Reel size | Tape width | Quantity (pcs) |
|--------------|-----------------|-----------|------------|----------------|
| KJ0603QD     | PDFN 3.3x3.3-8L | 13"       | 12 mm      | 5000           |

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

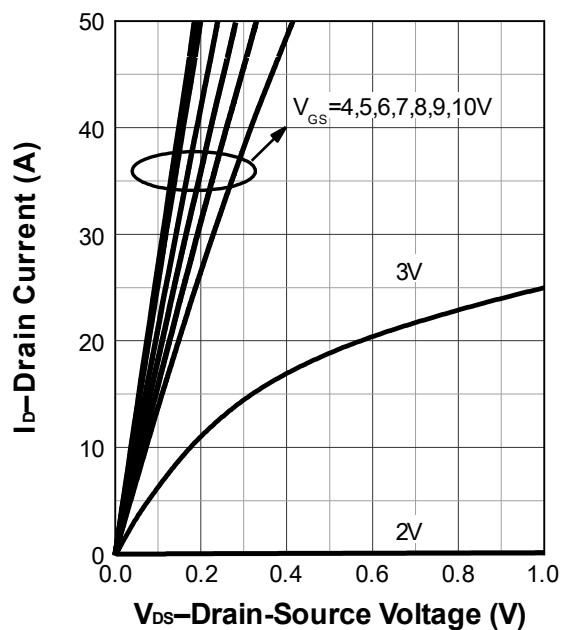
## 6. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

| Symbol                      | Parameter                       | Conditions                                                                                   | Min | Typ | Max  | Unit |
|-----------------------------|---------------------------------|----------------------------------------------------------------------------------------------|-----|-----|------|------|
| Static Characteristics      |                                 |                                                                                              |     |     |      |      |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage  | V <sub>GS</sub> =0 V, I <sub>DS</sub> =250 μA                                                | 30  | -   | -    | V    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage          | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250 μA                                   | 1.0 | -   | 2.2  | V    |
| I <sub>DSS</sub>            | Zero Gate Voltage Drain Current | V <sub>DS</sub> =30 V, V <sub>GS</sub> =0 V                                                  | -   | -   | 1    | μA   |
| I <sub>GSS</sub>            | Gate Leakage Current            | V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V                                                 | -   | -   | ±100 | nA   |
| R <sub>DS(ON)</sub>         | On-State Resistance             | V <sub>GS</sub> =10 V, I <sub>DS</sub> =10 A                                                 | -   | 5   | 6    | mΩ   |
|                             |                                 | V <sub>GS</sub> =4.5 V, I <sub>DS</sub> =5 A                                                 | -   | 8   | 11   |      |
| Diode Characteristics       |                                 |                                                                                              |     |     |      |      |
| V <sub>SD</sub>             | Diode Forward Voltage           | I <sub>SD</sub> =10 A, V <sub>GS</sub> =0 V                                                  | -   | 0.8 | 1.2  | V    |
| t <sub>rr</sub>             | Reverse Recovery Time           | I <sub>DS</sub> =10 A, V <sub>GS</sub> =0V,<br>dI <sub>SD</sub> /dt=100 A/μs                 | -   | 21  | -    | ns   |
| Q <sub>rr</sub>             | Reverse Recovery Charge         |                                                                                              | -   | 7   | -    | nC   |
| Dynamic Characteristics     |                                 |                                                                                              |     |     |      |      |
| C <sub>iss</sub>            | Input Capacitance               | V <sub>GS</sub> =0 V, V <sub>DS</sub> =15 V,<br>Frequency=1.0 MHz                            | -   | 600 | -    | pF   |
| C <sub>oss</sub>            | Output Capacitance              |                                                                                              | -   | 260 | -    |      |
| C <sub>rss</sub>            | Reverse Transfer Capacitance    |                                                                                              | -   | 15  | -    |      |
| R <sub>g</sub>              | Gate resistance                 |                                                                                              | -   | 1.3 | -    | Ω    |
| t <sub>d(on)</sub>          | Turn-on Delay Time              | V <sub>DS</sub> =15 V, V <sub>GEN</sub> =10 V,<br>R <sub>G</sub> =3 Ω, I <sub>DS</sub> =10 A | -   | 8   | -    | ns   |
| t <sub>r</sub>              | Turn-on Rise Time               |                                                                                              | -   | 29  | -    |      |
| t <sub>d(off)</sub>         | Turn-off Delay Time             |                                                                                              | -   | 22  | -    |      |
| t <sub>f</sub>              | Turn-off Fall Time              |                                                                                              | -   | 14  | -    |      |
| Gate Charge Characteristics |                                 |                                                                                              |     |     |      |      |
| Q <sub>g</sub>              | Total Gate Charge               | V <sub>DS</sub> =15 V, V <sub>GS</sub> =10 V,<br>I <sub>DS</sub> =10 A                       | -   | 7   | -    | nC   |
| Q <sub>gs</sub>             | Gate-Source Charge              |                                                                                              | -   | 2.5 | -    |      |
| Q <sub>gd</sub>             | Gate-Drain Charge               |                                                                                              | -   | 2   | -    |      |

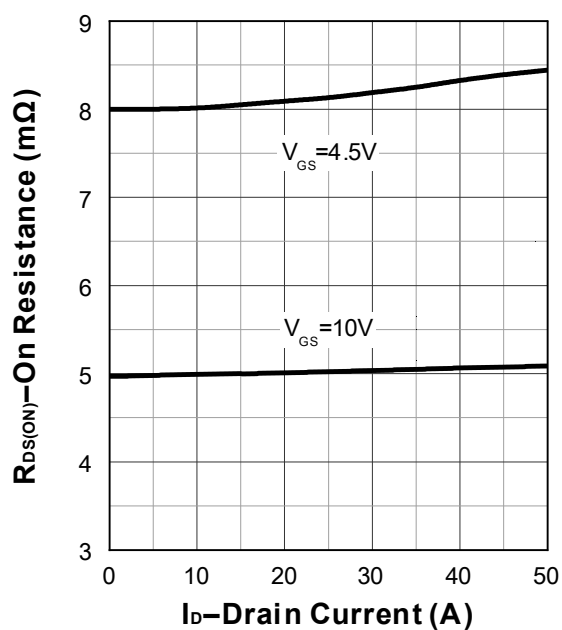
## **7. Typical Characteristics**

## 7. Typical Characteristics (cont.)

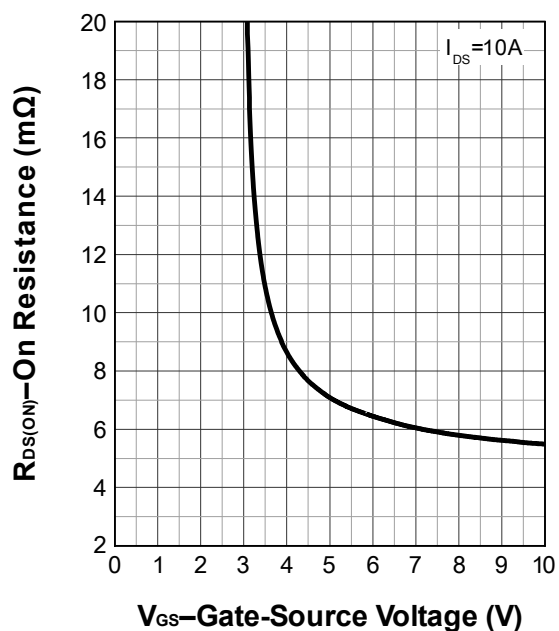
Output Characteristics



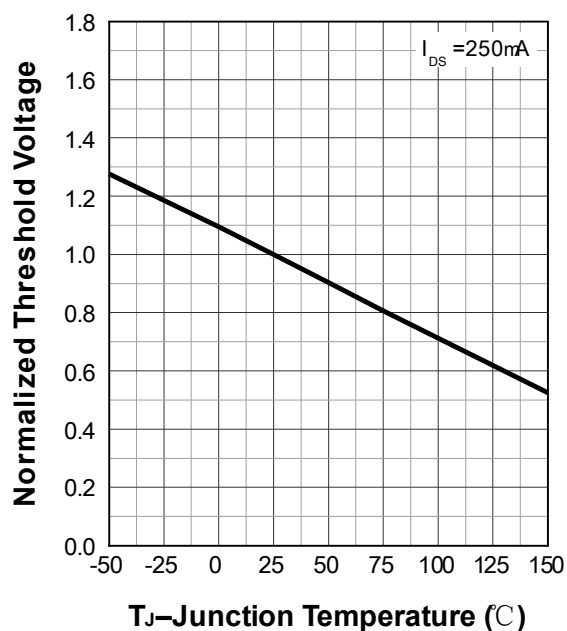
On Resistance



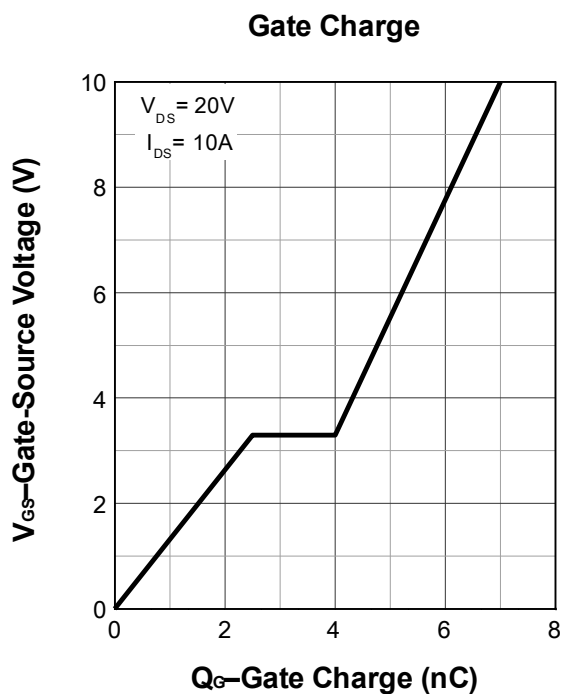
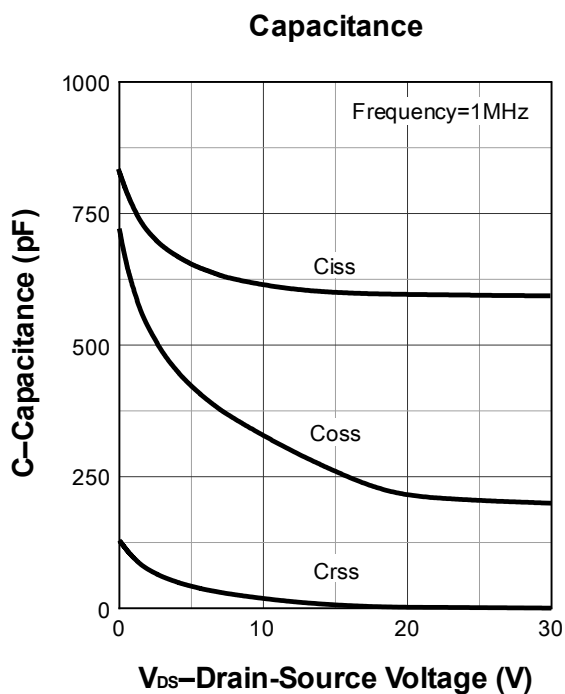
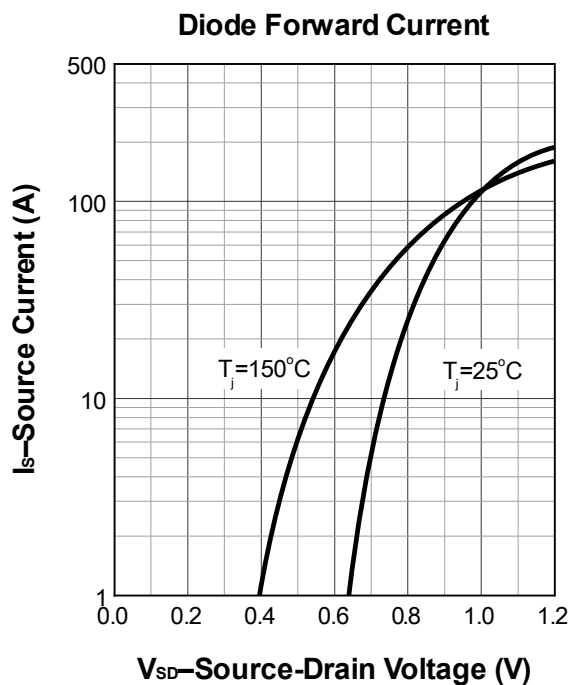
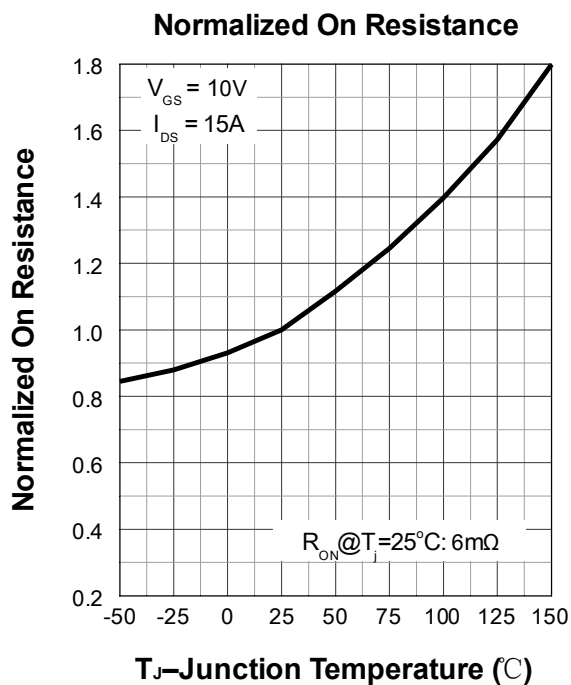
Transfer Characteristics



Normalized Threshold Voltage

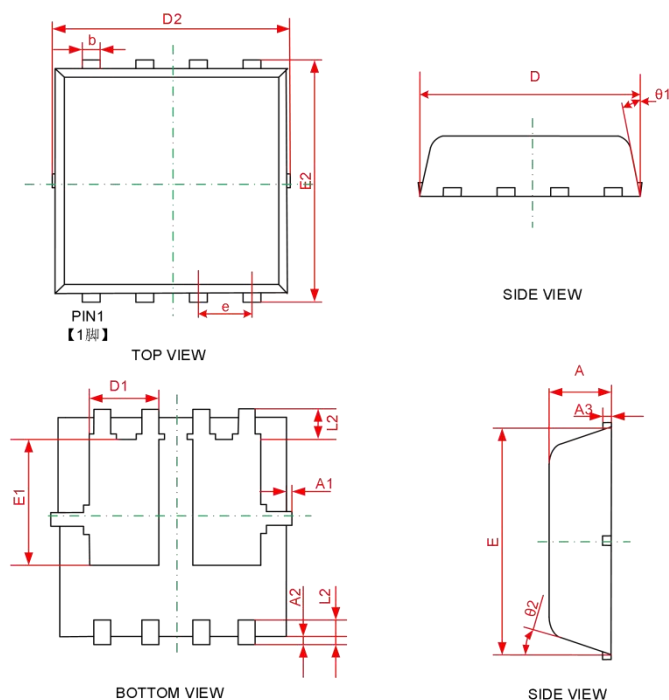


## 7. Typical Characteristics (cont.)



## 8. Package Dimensions

PDFN3.3x3.3-8L (Dual) package



| Symbol | Dimensions in Millimeters |       |
|--------|---------------------------|-------|
|        | Min                       | Max   |
| A      | 0.750                     | 0.850 |
| A1     | 0.000                     | 0.050 |
| A2     | 0.100                     | 0.200 |
| A3     | 0.152 REF.                |       |
| b      | 0.200                     | 0.400 |
| D      | 3.050                     | 3.250 |
| D1     | 0.935                     | 1.135 |
| D2     | 3.200                     | 3.400 |
| E      | 2.900                     | 3.100 |
| E1     | 1.635                     | 1.835 |
| E2     | 3.150                     | 3.350 |
| e      | 0.625                     | 0.675 |
| L1     | 0.350                     | 0.450 |
| L2     | 0.365                     | 0.465 |
| θ1     | 10°                       | 12°   |
| θ2     | 10°                       | 12°   |